



AF/2826

Atty. Docket No. 8013-1055

PATENTS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

BOX AF

Atsushi YAMAGUCHI et al.

Confirmation No. 6543

Serial No. 09/816,754

GROUP 2826

Filed March 26, 2001

Examiner Remmon R Forde

NITRIDE BASED SEMICONDUCTOR
PHOTO-LUMINESCENT DEVICE

AMENDMENT AFTER FINAL REJECTION

Commissioner for Patents

Washington, D.C. 20231

Sir:

Responsive to the Official Action of January 28, 2003,
please amend the above-identified application as follows:

IN THE SPECIFICATION:

A substitute specification is provided herewith.

REMARKS

As requested, a substitute specification accompanies this response. No new matter has been entered in the substitute specification. A marked-up copy of the original specification also accompanies this response showing the changes thereto. The amendments in the previous response have been entered in the substitute specification.

The claims were not rejected in view of prior art and thus it is presumed that they contain patentable subject matter.

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NITRIDE BASED SEMICONDUCTOR
PHOTO-LUMINESCENT DEVICE

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11. 9/28/04

SUPPLEMENTAL AMENDMENT AFTER FINAL REJECTION

Commissioner for Patents
PO Box 1450
Alexandria, Virginia 22313-1450

Sir:

In further response to the Official Action of January 28, 2003, and responsive to the requirement to file a statement of the substance of the interview conducted on May 6, 2003, as set forth in the Examiner Interview Summary Record mailed May 7, 2003, please amend the above-identified application as follows:

Kindly make of record the attached literature material:

GÖTZ et al., "Activation energies of Si donors in GaN,"
Appl. Phys. Lett. **68** (22), pp. 3144-3146 (1996); and

Introduction to Nitride Semiconductor Blue Lasers and
Light Emitting Diodes, p. 135, Ed. NAKAMURA et al., Publ. Taylor
& Francis (2000).

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